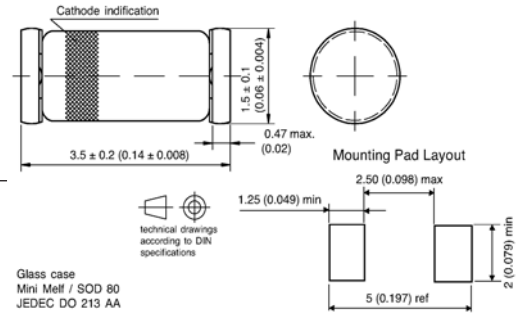


Features

- ◆ Silicon Epitaxial Planar Diode
- ◆ Fast switching diode in MiniMELF case especially suited for automatic insertion.
- ◆ This diode is also available in other case styles including the DO-35 case with the type designation 1N4151.

Mechanical Data

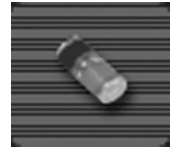
- ◆ Case: MiniMELF Glass Case (SOD-80C)
- ◆ Weight: approx. 0.05g
- ◆ Cathode Band Color: Black



Maximum Ratings and Thermal Characteristics

(T_A=25°C unless otherwise noted.)

Parameter	Symbol	Limit	Unit
Reverse voltage	V _R	50	Volts
Peak reverse voltage	V _{RM}	75	Volts
Forward DC current at T _{amb} =25°C ⁽¹⁾	I _F	200	mA
Average rectified current (half wave rectification with resist. load at T _{amb} =25°C f≥50Hz) ⁽¹⁾	I _{F(AV)}	150	mA
Surge forward current at t<1s and T _J =25°C	I _{FSM}	500	mA
Power dissipation at T _{amb} =25°C ⁽¹⁾	P _{tot}	500	mW
Thermal resistance junction to ambient air ⁽¹⁾	R _{θJA}	350	°C/W
Junction temperature	T _J	175	°C
Storage temperature range	T _S	-65 to +175	°C



Electrical Characteristics

(T_J=25°C unless otherwise noted.)

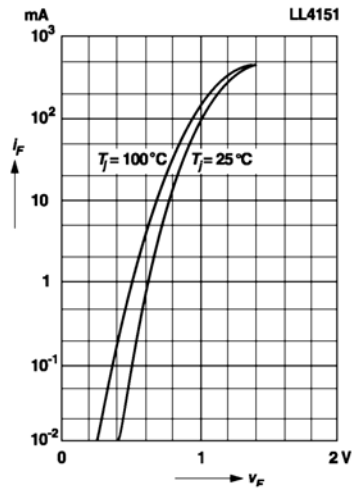
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage	V _F	I _F =50mA	-	-	1.0	Volt
Leakage current	I _R	V _R =50V, T _J =150°C	-	-	50 50	nA μA
Capacitance	C _{tot}	V _F =V _R =0V	-	-	2.0	pF
Reverse recovery time	t _{rr}	I _F =10mA, I _R =10mA I _F =1mA, R _L =100Ω I _R =10mA, I _F =1mA V _R =6V, R _L =100Ω	- -	- -	4.0 2.0	ns
Rectification efficiency (see third Page)	η _v	f=100MHz, V _{RR} =2V	0.45	-	-	-

Notes: 1. Valid provided that electrodes are kept at ambient temperature

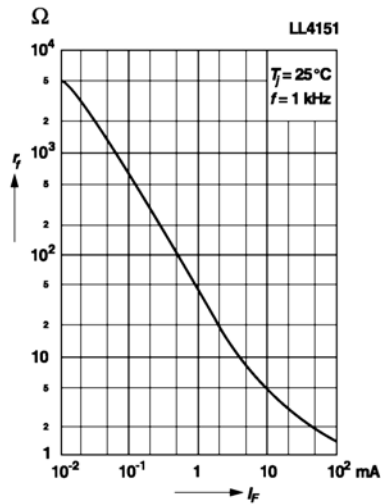
RATINGS AND CHARACTERISTIC CURVES

($T_A = 25^{\circ}\text{C}$ unless otherwise noted.)

Forward characteristics

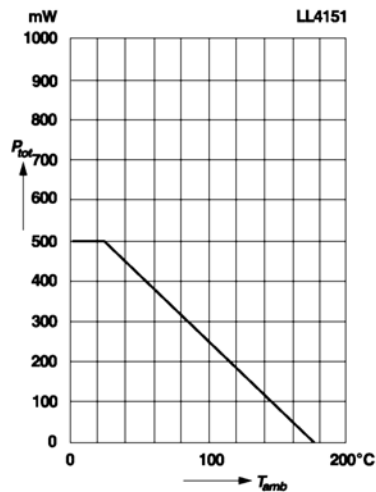


Dynamic forward resistance versus forward current

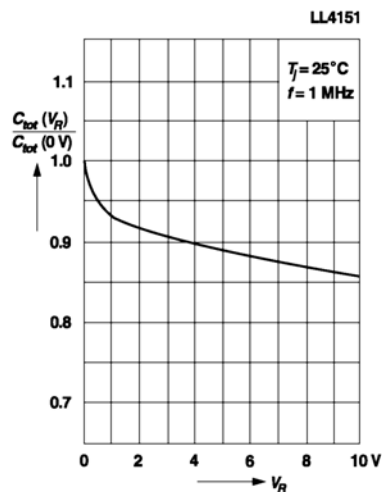


Admissible power dissipation versus ambient temperature

Valid provided that electrodes are kept at ambient temperature



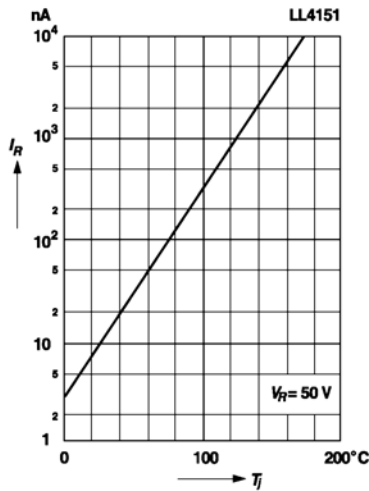
Relative capacitance versus reverse voltage



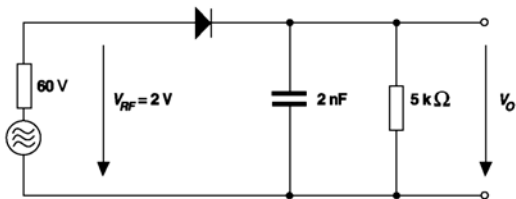
RATINGS AND CHARACTERISTIC CURVES

($T_A = 25^{\circ}\text{C}$ unless otherwise noted.)

Leakage current
versus junction temperature



Rectification Efficiency Measurement Circuit



Admissible repetitive peak forward current versus pulse duration

Valid provided that electrodes are kept at ambient temperature

